

3Q Hi-Com Triac Rev. 3 — 23 June 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78D (TO-220AB) plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series C" triac will commutate the full RMS current at the maximum rated junction temperature without the aid of a snubber. This device has high junction temperature operating capability and an internally isolated mounting base.

1.2 Features and benefits

- 2500 V RMS isolation voltage capability
- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High junction temperature operating capability

1.3 Applications

- Electronic thermostats (heating and cooling)
- High power motor controls e.g. vacuum cleaners

1.4 Quick reference data

Table 1. Quick reference data

- High surge capability
- High voltage capability
- Internally insulated package
- Internally isolated mounting base
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

	Quick reference und					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see Figure 4; see Figure 5	-	-	160	A
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 108 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	16	A



Table 1.	Quick reference data	continued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; see <u>Figure 7</u>	2	-	35	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; see <u>Figure 7</u>	2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{2}$	2	-	35	mA

Pinning information 2.

Table 2.	Pinning	g information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N 1
2	T2	main terminal 2	mb	T2-T1
3	G	gate	r O h	`G sym051
mb	n.c.	mounting base; isolated		

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Ordering information 3.

Table 3. **Ordering information**

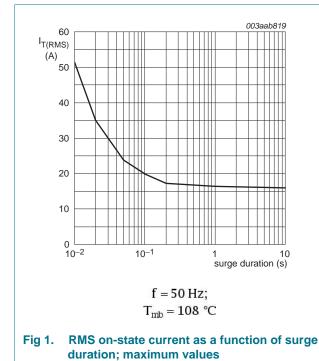
Type number	Package			
	Name	Description	Version	
BTA416Y-600C	TO-220AB	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220	SOT78D	

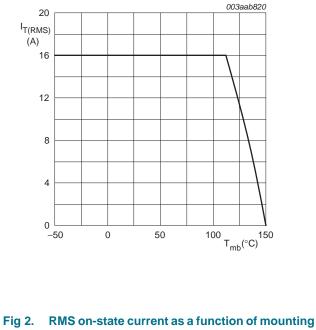
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 108 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	16	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	160	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	176	А
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	128	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu \text{s}$	-	100	A/µs
I _{GM}	peak gate current		-	4	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

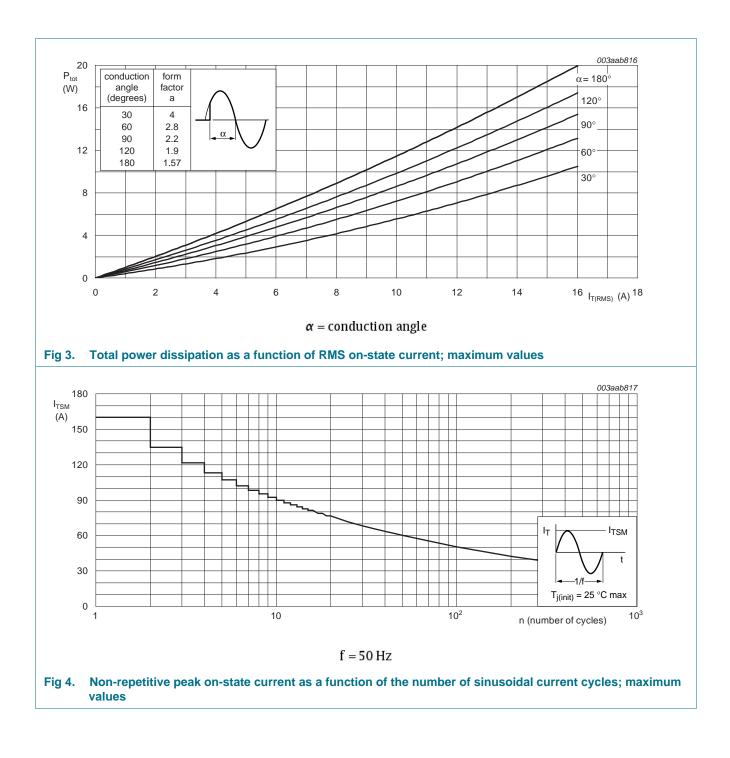




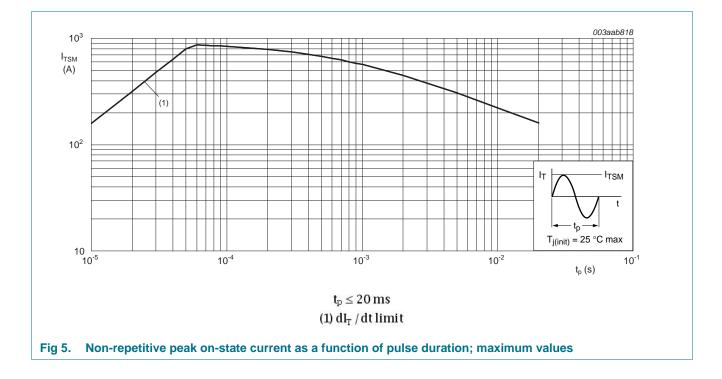
ig 2. RMS on-state current as a function of mounting base temperature; maximum values

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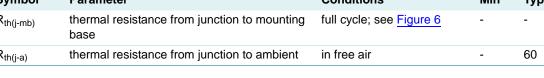


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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	full cycle; see Figure 6	-	-	1.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



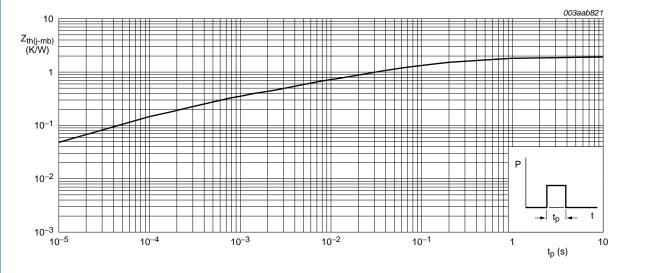


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

Isolation characteristics 6.

Table 6.	Isolation characteristics	
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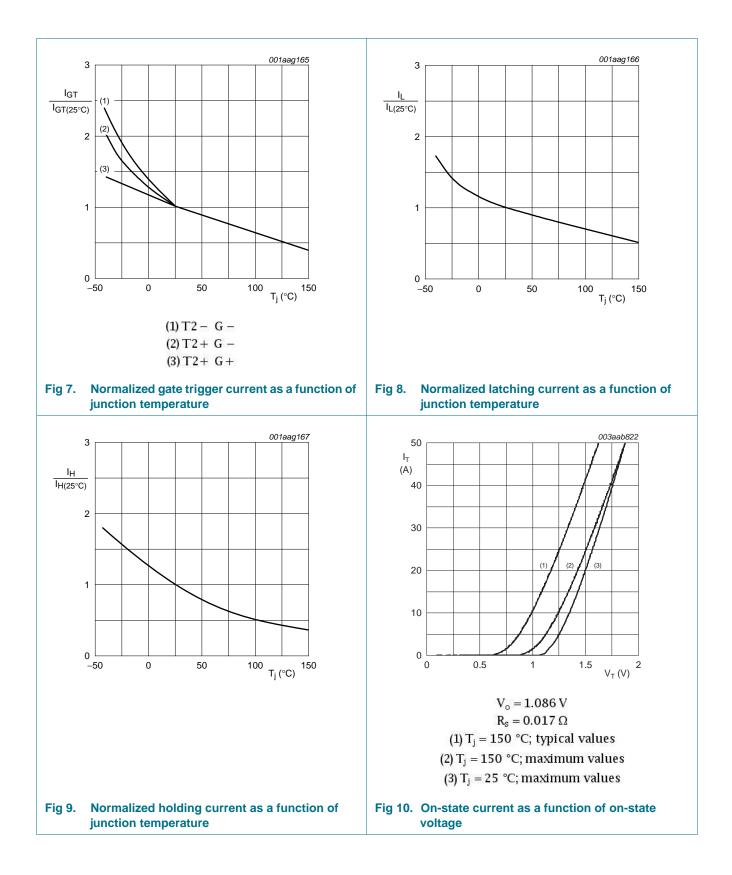
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free ; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _{mb} = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink ; $f = 1 \text{ MHz}$; $T_{mb} = 25 \text{ °C}$	-	10	-	pF

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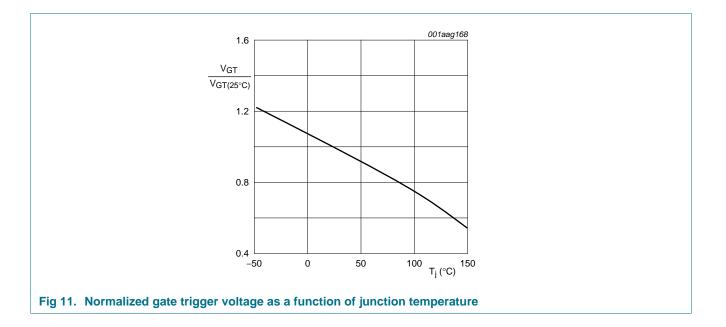
7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2+ G+}; \text{T}_j = 25 \text{ °C};$ see Figure 7	2	-	35	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2+ G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 7	2	-	35	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 7	2	-	35	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{T2+ G+}; \text{T}_j = 25 \text{ °C};$ see Figure 8	-	-	50	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 8	-	-	60	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-}; \text{ T}_j = 25 \text{ °C};$ see Figure 8	-	-	50	mA
I _H	holding current	$V_D = 12 \text{ V}; \text{ T}_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{100000000000000000000000000000000000$	-	-	35	mA
V _T	on-state voltage	I _T = 20 A; T _j = 25 °C; see <u>Figure 10</u>	-	1.2	1.5	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; see <u>Figure 11</u>	-	0.7	1.5	V
		$V_D = 400 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T}_j = 150 ^\circ\text{C}$	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
		V _D = 600 V; T _j = 150 °C	-	0.4	2	mA
Dynamic of	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; exponential waveform; gate open ciucuit	500	-	-	V/µs
		V_{DM} = 402 V; T _j = 150 °C; exponential waveform; gate open circuit	300	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 20 \text{ V}/\mu \text{s};$ (without snubber condition); gate open circuit	10	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 150 \text{ °C}; I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 20 \text{ V}/\mu\text{s};$ (without snubber condition); gate open circuit	4	-	-	A/ms
t _{gt}	gate-controlled turn-on time	I_{TM} = 20 A; V _D = 600 V; I _G = 100 mA; dI _G /dt = 5 A/µs	-	2	-	μs

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8. Package outline

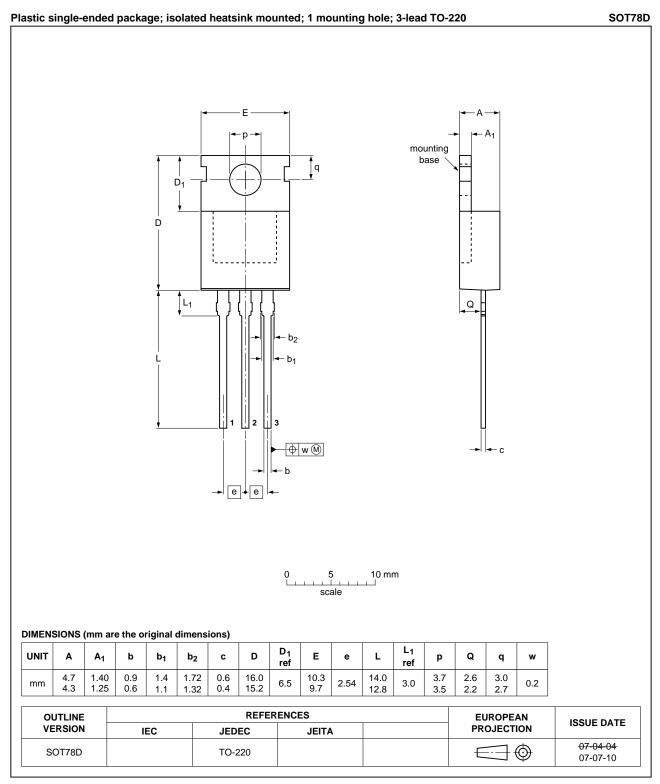


Fig 12. Package outline SOT78D (TO-220AB)



9. Revision history

Table 8. Revision histo	ry			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA416Y-600C v.3	20110623	Product data sheet	-	BTA416Y_SER_B_C v.1
Modifications:	 Type numbe 	r BTA416Y-600C separa	ed from data sheet E	BTA416Y_SER_B_C v.1.
	 Various char 	iges to content.		
BTA416Y_SER_B_C v.1	20080311	Product data sheet	-	-

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10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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